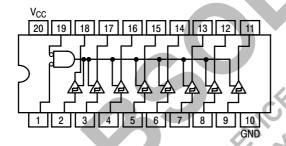
Octal Buffer/Line Driver with 3-State Outputs

The SN74LS541 is an octal buffer and line driver with the same functions as the LS241, but with pinouts on the opposite side of the package.

This device type is designed to be used as a memory address driver, clock driver and bus-oriented transmitter/receiver. This device is especially useful as output ports for the microprocessors, allowing ease of layout and greater PC board density.

- Hysteresis at Inputs to Improve Noise Margin
- PNP Inputs Reduce Loading
- 3-State Outputs Drive Bus Lines
- Inputs and Outputs Opposite Side of Package, Allowing Easier Interface to Microprocessors
- Input Clamp Diodes Limit High-Speed Termination Effects

LOGIC AND CONNECTION DIAGRAM DIP (TOP VIEW)



GUARANTEED OPERATING RANGES

Symbol	Parameter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage	4.75	5.0	5.25	V
T _A	Operating Ambient Temperature Range	0	25	70	°C
I _{OH}	Output Current - High			-15	mA
I _{OL}	Output Current – Low	O.		24	mA



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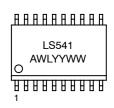
LOW POWER SCHOTTKY



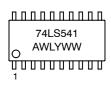


CASE 738









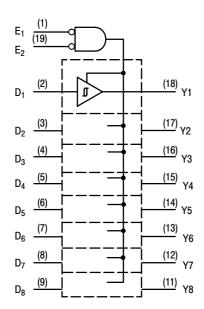
A = Assembly Location
WL = Wafer Lot
Y, YY = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
SN74LS541N	PDIP-20	1440 Units/Box
SN74LS541DW	SOIC-WIDE	38 Units/Rail
SN74LS541DWR2	SOIC-WIDE	2500/Tape & Reel
SN74LS541M	SOEIAJ-20	See Note 1
SN74LS541MEL	SOEIAJ-20	See Note 1

 For ordering information on the EIAJ version of the SOIC package, please contact your local ON Semiconductor representative.

BLOCK DIAGRAM



INPUTS			OUTPUTS		
E ₁	E ₂	D	LS540	LS541	
L	L	Н	L	П	
Н	X	Х	Z	Z	
Χ	Н	Х	Z	Z	
L	┙	L	Ι	L	

L = LOW Voltage Level

H = HIGH Voltage Level X = Immaterial

Z = High Impedance

DC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (unless otherwise specified)

			Limits		· ·	(°, °O, °		
Symbol	Parameter	Min	Тур	Max	Unit	Test	t Conditions	
V _{IH}	Input HIGH Voltage	2.0			200	Guaranteed Input All Inputs	HIGH Voltage for	
V _{IL}	Input LOW Voltage			0.8	V	Guaranteed Input All Inputs	Guaranteed Input LOW Voltage for All Inputs	
V _{IK}	Input Clamp Diode Voltage		-0.65	-1.5	V	V _{CC} = MIN, I _{IN} = -	- 18 mA	
· · · · · · · · · · · · · · · · · · ·	Output HIGH Voltage	2.4	3.4	O,	V	V _{CC} = MIN, I _{OH} =	-3.0 mA	
V _{OH}	Output high voltage	2.0	1		V	$V_{CC} = MIN$, $I_{OH} = MAX$, $V_{IL} = 0.5 V$		
			0.25	0.4	V	I _{OL} = 12 mA	V _{CC} = V _{CC} MIN,	
V _{OL}	Output LOW Voltage	10	0.35	0.5	V	I _{OL} = 24 mA	V _{IN} = V _{IL} or V _{IH} per Truth Table	
$V_{T+}-V_{T-}$	Hysteresis	0.2	0.4		V	V _{CC} = MIN		
I _{OZH}	Output Off Current HIGH			20	μΑ	V _{CC} = MAX, V _{OU}	_T = 2.7 V	
l _{OZL}	Output Off Current LOW			-20	μΑ	V _{CC} = MAX, V _{OU}	_T = 0.4 V	
I	Input HICH Current			20	μΑ	V _{CC} = MAX, V _{IN} =	= 2.7 V	
I _{IH}	Input HIGH Current			0.1	mA	V _{CC} = MAX, V _{IN} =	= 7.0 V	
I _{IL}	Input LOW Current			-0.2	mA	V _{CC} = MAX, V _{IN} =	= 0.4 V	
Ios	Short Circuit Current (Note 1)	-40		-225	mA	V _{CC} = MAX		
	Power Supply Current Total, Output HIGH	_	_	32	mA			
I _{CC}	Total, Output LOW			52	mA	V _{CC} = MAX		
	Total Output 3-State			55	mA			

Not more than one output should be shorted at a time, nor for more than 1 second.

AC CHARACTERISTICS $(T_A = 25^{\circ}C)$

			Limits			
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
t _{PLH}	Propagation Delay,		12	15		
t _{PHL}	Data to Output		12	18	ns	V -50V
t _{PZH}	Output Enable Time to HIGH Level		15	32	ns	V_{CC} = 5.0 V C_L = 45 pF R_L = 667 Ω
t _{PZL}	Output Enable Time to LOW Level		20	38	ns	_
t _{PHZ}	Output Disable Time to HIGH Level		10	18	ns	0 50.5
t _{PLZ}	Output Disable Time to LOW Level		15	29	ns	C _L = 5.0 pF

AC WAVEFORMS

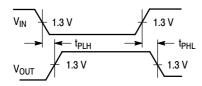


Figure 1.

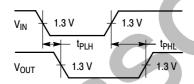


Figure 2.

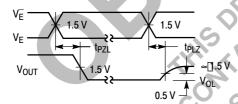


Figure 3.

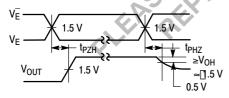
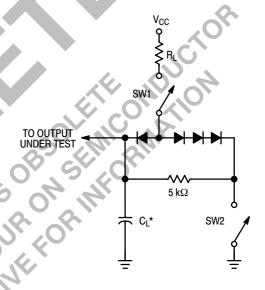


Figure 4.



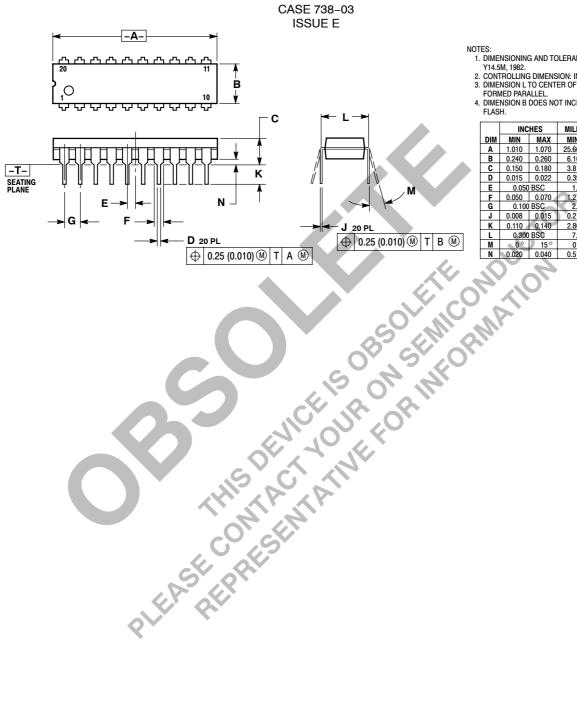
SWITCH POSITIONS

SYMBOL	SW1	SW2
t _{PZH}	Open	Closed
t _{PZL}	Closed	Open
t _{PLZ}	Closed	Closed
t _{PHZ}	Closed	Closed

Figure 5.

PACKAGE DIMENSIONS





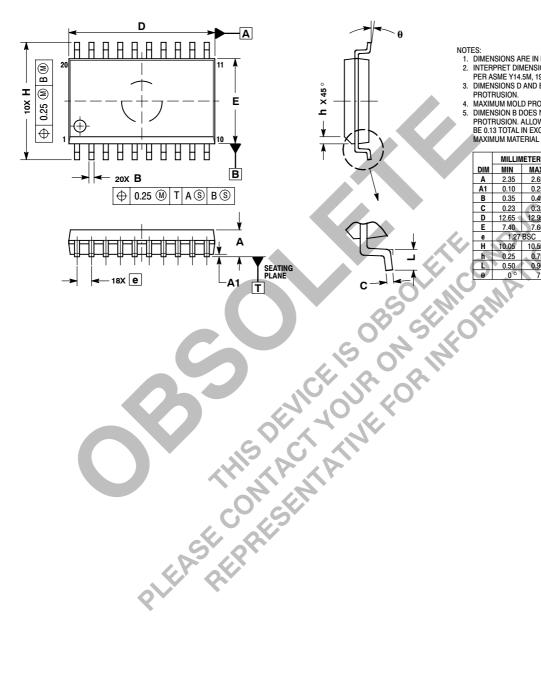
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- 1. DIMENSIONING AND TOLERANCING FER AL Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL. 4. DIMENSION B DOES NOT INCLUDE MOLD
- FLASH.

	INC	HES	MILLIN	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
C	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
E	0.050	BSC	1.27 BSC		
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300	BSC	7.62	BSC	
M	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

PACKAGE DIMENSIONS

D SUFFIX PLASTIC SOIC PACKAGE CASE 751D-05 **ISSUE F**



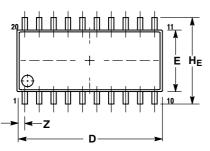
- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL
 BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

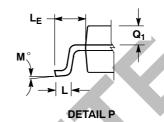
	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
H ⁴	10.05	10.55			
h	0.25	0.75			
(L)	0.50	0.90			
A	0 °	7 °			

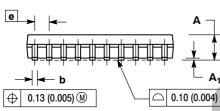
PACKAGE DIMENSIONS

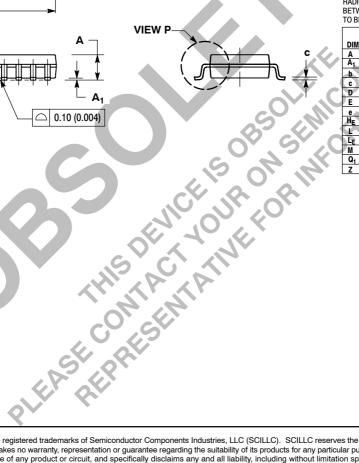
M SUFFIX

SOEIAJ PACKAGE CASE 967-01 ISSUE O









NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT, MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIÑ	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A₁_`	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
c	0.18	0.27	0.007	0.011	
D	12.35	12.80	0.486	0.504	
E	5.10	5.45	0.201	0.215	
e 👝	1.27	BSC	0.050 BSC		
HE	7.40	8.20	0.291	0.323	
	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
М	0 °	10 °	0 °	10 °	
Q_1	0.70	0.90	0.028	0.035	
Z		0.81		0.032	

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